

**IN THE SPECIFICATION:**

**Please amend the specification as follows:**

[0004] Patent Application Serial No. 60/339,089 now abandoned 10/316,254 (Attorney Docket No. YOR 9 2001-0774US2) herein incorporated by reference, describes a MEMS RF resonator fabrication process which utilizes IC compatible processes for fabrication of MEMS resonators and filters. In particular, the release method and encapsulation processes used and applied to the fabrication of RF MEMS switches.

[0005] ~~Patent Application Serial No. 10/150,285 (Attorney Docket No. YOR9 2002-0021)~~ U.S. Patent No. 6,876,282 to Deligianni et al. of common assignee, herein incorporated by reference, describes the design of a MEMS RF switch wherein the actuators being totally decoupled from the RF signal carrying electrodes in a series switch. If the actuation and RF signal electrodes are not physically separated and are part of the closing mechanism (by including one of the actuator electrodes) it may cause the switch to close (hot switching), thus limiting the switch linearity by generation of harmonics. This is a known problem for transistor switches such as NMOS or FET. Thus, in order to minimize losses and improve the MEMS switch linearity, it is important to separate entirely the RF signal electrodes from the DC actuator electrodes. ~~Patent Application Serial No. 10/150,285 (Attorney Docket No. YOR9 2002-0021)~~ U.S. Patent No. 6,876,282 describes various designs of composite metal-insulator MEMS switches. The preferred metal used is, typically, copper, while the insulator is silicon dioxide, resulting in full separation of the actuators from the RF signal carrying electrodes. In addition, Patent Application Serial No. 10/315,335 ~~(Attorney Docket No. YOR9 2002-0221)~~ describes the use of a metal ground plane 3-4 microns below the MEMS switch to improve its insertion loss switch characteristics.